



SPP1305

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP1305 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

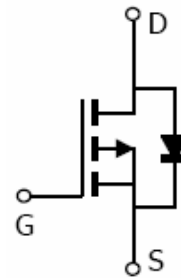
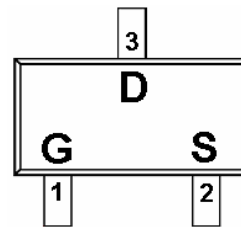
FEATURES

- ◆ -20V/-0.95A, $R_{DS(ON)}=280m\Omega@V_{GS}=-4.5V$
- ◆ -20V/-0.80A, $R_{DS(ON)}=380m\Omega@V_{GS}=-2.5V$
- ◆ -20V/-0.70A, $R_{DS(ON)}=530m\Omega@V_{GS}=-1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-323 (SC-70) package design

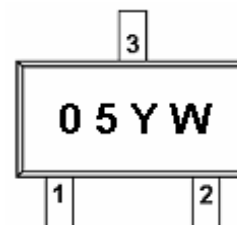
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION (SOT-323 ; SC-70)



PART MARKING



Y : Year Code
W : Week Code



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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP1305S32RG	SOT-323	05YW

※ Week Code : A ~ Z (1 ~ 26) ; a ~ z (27 ~ 52)

※ SPP1305S32RG : Tape Reel ; Pb – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	-20	V	
Gate –Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-1.0	A
		T _A =70°C	-0.7	
Pulsed Drain Current	I _{DM}	-3	A	
Continuous Source Current(Diode Conduction)	I _S	-0.28	A	
Power Dissipation	P _D	T _A =25°C	0.33	W
		T _A =70°C	0.21	
Operating Junction Temperature	T _J	-55/150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	
Thermal Resistance-Junction to Ambient	R _{θJA}	105	°C/W	



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ELECTRICAL CHARACTERISTICS

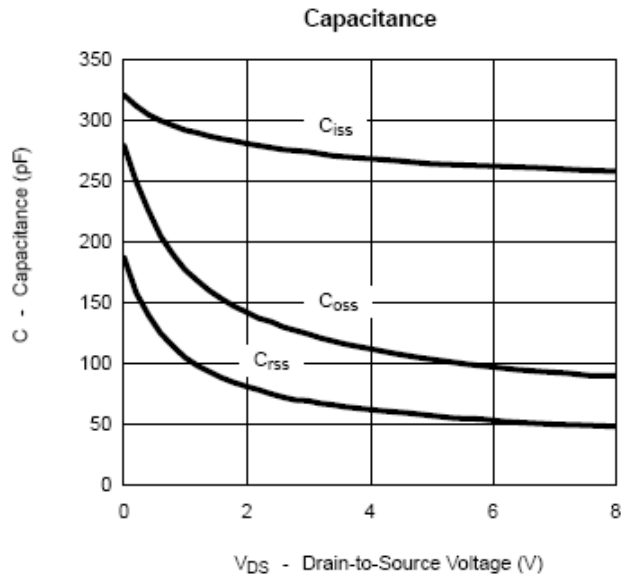
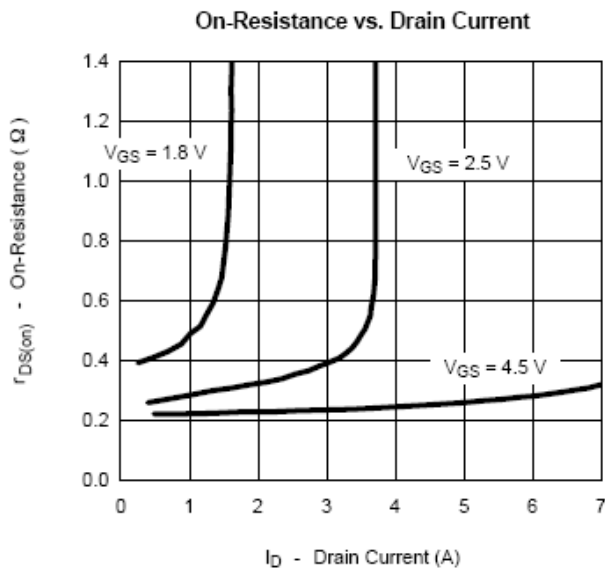
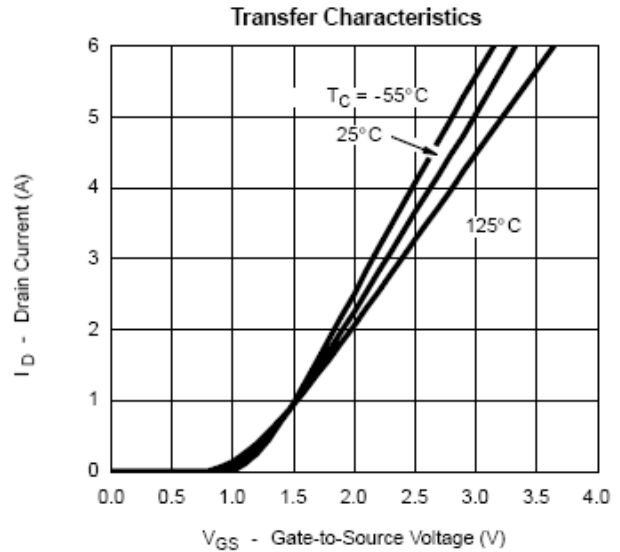
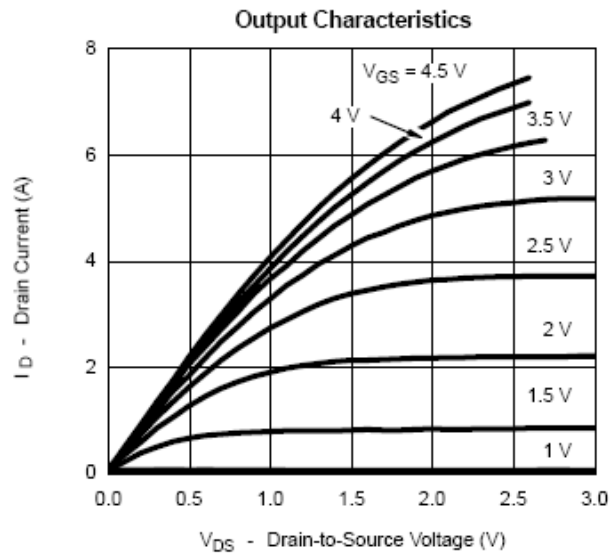
(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5		-1.2	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	uA
		$V_{DS}=-20V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-4.5V$	-6			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.95A$		0.22	0.28	Ω
		$V_{GS}=-2.5V, I_D=-0.80A$		0.30	0.38	
		$V_{GS}=-1.8V, I_D=-0.70A$		0.42	0.53	
Forward Transconductance	g_{fs}	$V_{DS}=-5V, I_D=-1.0A$		3.5		S
Diode Forward Voltage	V_{SD}	$I_S=-0.5A, V_{GS}=0V$		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-4V, V_{GS}=-4.5V$ $I_D=-1.0A$		3.0	4.2	nC
Gate-Source Charge	Q_{gs}			0.6		
Gate-Drain Charge	Q_{gd}			0.5		
Input Capacitance	C_{iss}	$V_{DS}=-4V, V_{GS}=0V$ $f=1MHz$		320		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			25		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-4V, R_L=4\Omega$ $I_D=-1.0A, V_{GEN}=-4.5V$ $R_G=6\Omega$		10	16	ns
	t_r			40	60	
Turn-Off Time	$t_{d(off)}$			18	25	
	t_f			15	20	



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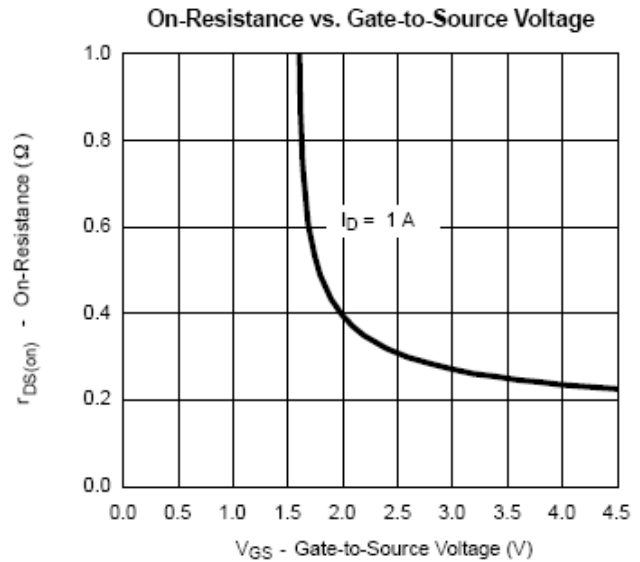
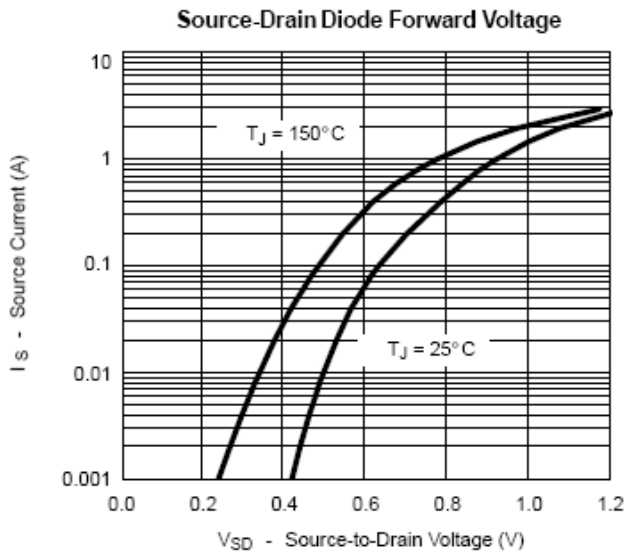
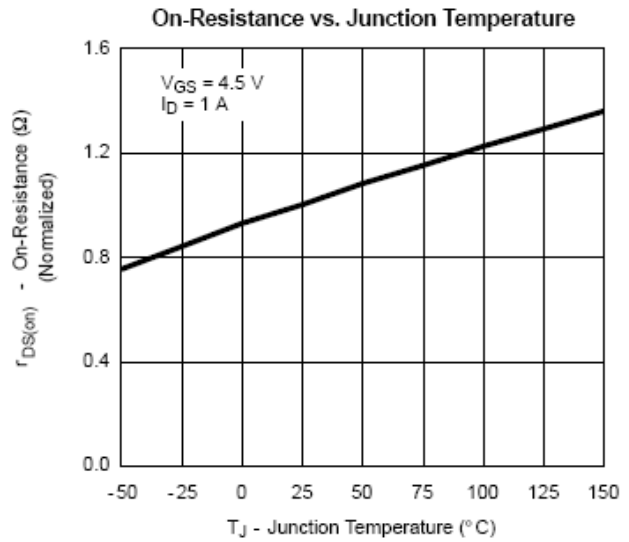
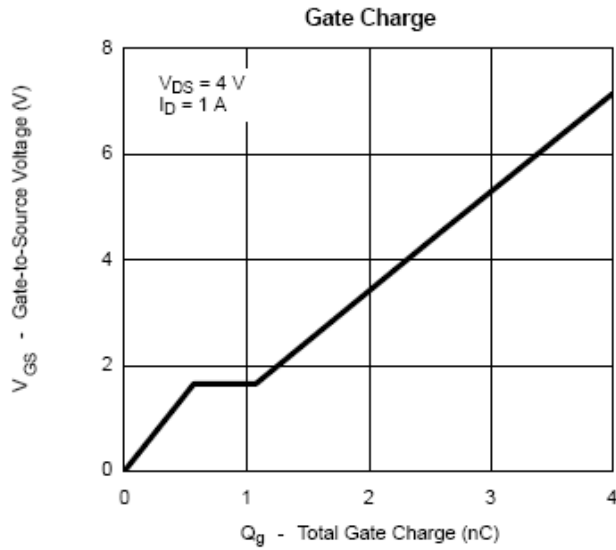
TYPICAL CHARACTERISTICS





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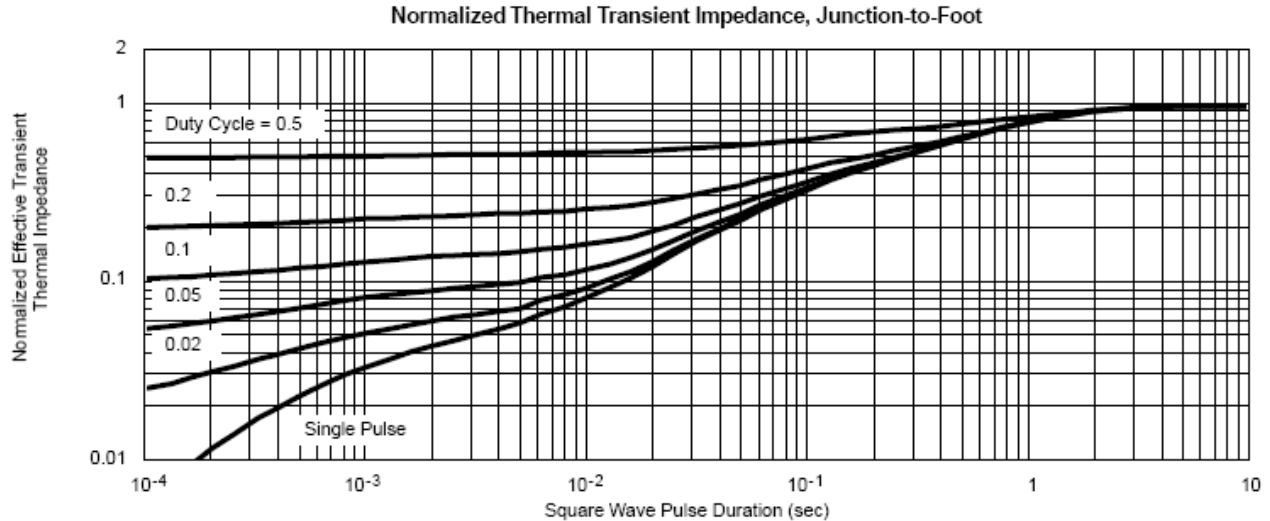
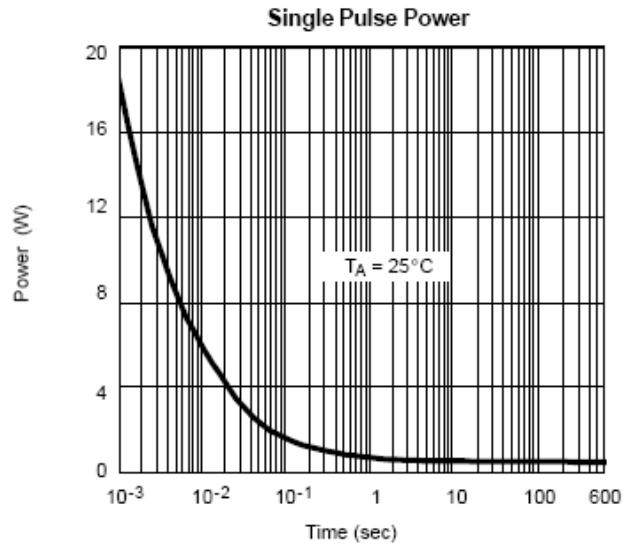
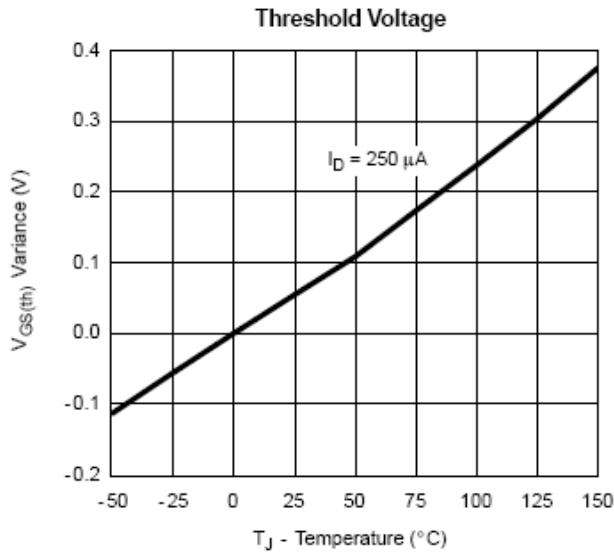
TYPICAL CHARACTERISTICS





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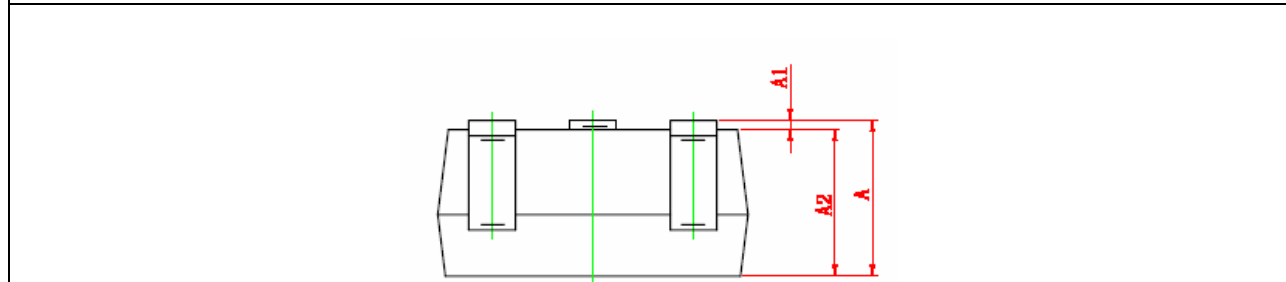
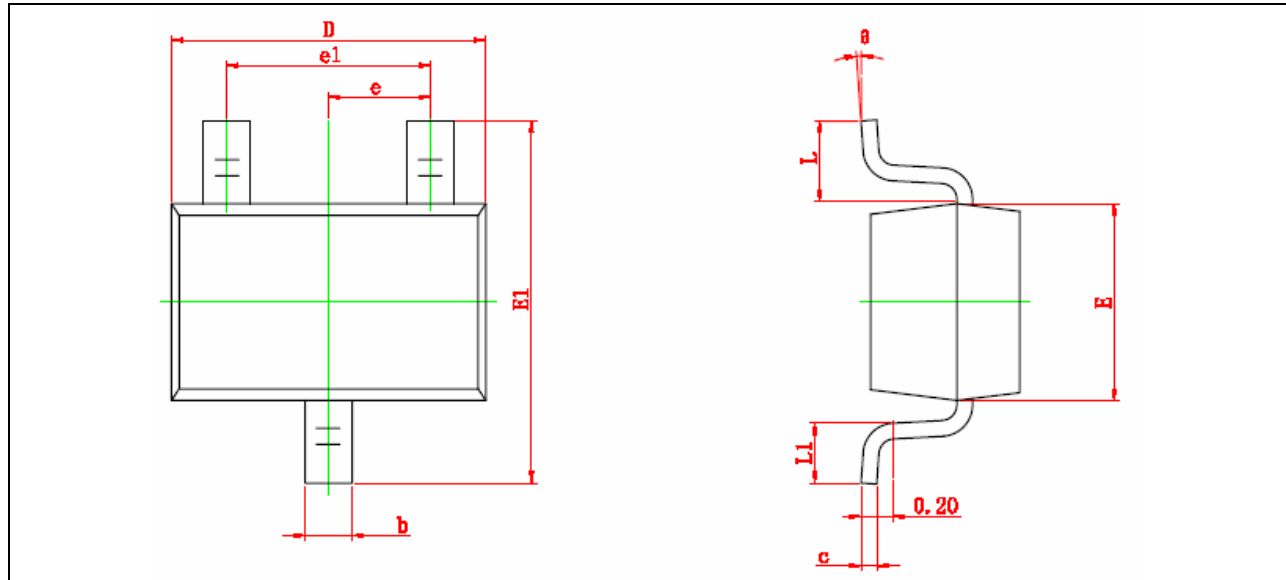
TYPICAL CHARACTERISTICS





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SOT-323 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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SYNC Power Corporation

9F-5, No.3-2, Park Street

NanKang District (NKSP), Taipei, Taiwan 115

Phone: 886-2-2655-8178

Fax: 886-2-2655-8468

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